

1200V 600A CoolFAST™ IGBT7 Power Module

Electrical Features:

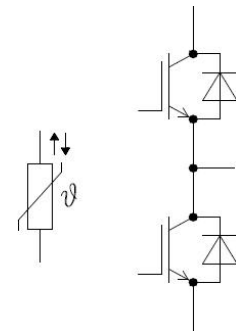
- 1200V 600A, $V_{CE(sat)} = 2.0V@25^{\circ}C$
- High RBSOA Capability
- Trench/FS Technology
- Low Reverse-recovery Losses
- High SC Capability

Applications:

- Motor Drives
- Solar Applications
- UPS Systems
- Commercial Electric Vehicles
- Wind Turbines

Mechanical Features:

- High Power and Thermal Cycling Capability
- Maximum Junction Temperature 175°C
- High Power Density
- PressFIT Contact Technology
- Isolated Base Plate



Equivalent circuit

Maximum Ratings and Characteristics

Absolute Maximum Ratings at $T_c = 25^{\circ}C$ (unless otherwise specified)

Items	Symbols	Values	Units	Remarks
Collector-Emitter voltage	V_{CES}	1200	V	
Gate-Emitter voltage	V_{GES}	± 30	V	
DC Collector Current	I_C	600	A	$T_c = 100^{\circ}C$
Pulsed Collector Current	I_{CP}	1200	A	Note *1
Diode Forward Current	I_F	600	A	
Repetitive Peak Forward Current	I_{FRM}	1200	A	
Operating Junction Temperature	T_{vj}	-40 ~ +150	$^{\circ}C$	
Storage Temperature	T_{stg}	-40 ~ +125	$^{\circ}C$	

Note *1 : Pulse width limited by T_{vjmax} .

Electrical characteristics (unless otherwise specified)
IGBT, Inverter

Description	Symbols	Conditions	Values			Unit	
			Min	Typ	Max		
Zero Gate Voltage Collector Current	I_{CES}	$V_{CE}= 1200V, V_{GE}= 0V$ $T_{vj}= 25^{\circ}C$			200	μA	
Gate-Emitter Leakage Current	I_{GES}	$V_{CE}= 0V, V= 20V, T_{vj}= 25^{\circ}C$			± 300	nA	
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE}= V_{GE}, I_C= 600mA$	6.2	6.7	7.2	V	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE}= 15V$ $I_C= 600A$	$T_{vj}= 25^{\circ}C$		2.0	2.4	V
			$T_{vj}= 125^{\circ}C$		2.5		
			$T_{vj}= 150^{\circ}C$		2.7		
Input Capacitance	C_{ies}	$V_{CE}= 25V, V_{GE}= 0V$		128.8		nF	
Reverse Transfer Capacitance	C_{res}	$f= 1MHz$		0.76		nF	
Gate Charge	Q_G	$V_{CC}= 600V, V_{GE}= 15V$		2270		nC	
Internal Gate Resistor	R_{Gint}	$T_{vj}= 25^{\circ}C$		1.50		Ω	
Turn-On Delay Time, Inductive load	$t_{d(on)}$		$T_{vj}= 25^{\circ}C$		1.09	μs	
			$T_{vj}= 125^{\circ}C$		1.02		
			$T_{vj}= 150^{\circ}C$		0.98		
Rise Time, Inductive load	t_r		$T_{vj}= 25^{\circ}C$		0.53	μs	
			$T_{vj}= 125^{\circ}C$		0.55		
			$T_{vj}= 150^{\circ}C$		0.57		
Turn-Off Delay Time, Inductive load	$t_{d(off)}$	$V_{CC}= 600V$ $I_C= 600A$	$T_{vj}= 25^{\circ}C$		1.60	μs	
			$T_{vj}= 125^{\circ}C$		1.65		
			$T_{vj}= 150^{\circ}C$		1.67		
Fall Time, Inductive load	t_f	$V_{GE}= 15V$ $R_G= 15\Omega$	$T_{vj}= 25^{\circ}C$		0.12	μs	
			$T_{vj}= 125^{\circ}C$		0.12		
			$T_{vj}= 150^{\circ}C$		0.13		
Turn-On Energy	E_{on}		$T_{vj}= 25^{\circ}C$		171	mJ	
			$T_{vj}= 125^{\circ}C$		210		
			$T_{vj}= 150^{\circ}C$		223		
Turn-Off Energy	E_{off}		$T_{vj}= 25^{\circ}C$		87	mJ	
			$T_{vj}= 125^{\circ}C$		95		
			$T_{vj}= 150^{\circ}C$		97		
SC Data	I_{sc}	$V_{CC}= 600V$ $R_G= 20\Omega$ $V_{GE} \leq 15V$ $V_{CEmax}=V_{CE-L_{SCE}}*di/dt$	$t_p \leq 10\mu s$ $T_{vj}= 150^{\circ}C$		2400	A	

Diode, Inverter

Description	Symbols	Conditions	Values			Unit
			Min	Typ	Max	
Forward Voltage	V _F	I _F = 600A V _{GE} = 0V	T _{vj} = 25°C	2.9	3.5	V
			T _{vj} = 125°C	2.25		
			T _{vj} = 150°C	2.15		
Recovery Charge	Q _r	I _F = 600A, V _R = 600V -di _F /dt= 1000A/us, V _{GE} = -8V	T _{vj} = 25°C	20.1		μC
			T _{vj} = 125°C	36.9		
			T _{vj} = 150°C	48.5		
Reverse Recovery Energy	E _{rec}	I _F =600A, V _R =600V -di _F /dt=1000A/us V _{GE} = -8V	T _{vj} = 25°C	3.9		mJ
			T _{vj} = 125°C	10.6		
			T _{vj} = 150°C	12.7		

NTC Characteristics

Description	Symbols	Conditions	Values			Unit
			Min	Typ	Max	
Rated Resistance	R ₂₅	T _{NTC} =25°C		5.0		KΩ
Deviation of R ₁₀₀	ΔR/R	T _{NTC} =100°C, R ₁₀₀ =493Ω	-5		5	%
Power Dissipation	P ₂₅				20	mW
B-value	B _{25/50}	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15K))]$		3380		K
B-value	B _{25/80}	$R_2=R_{25}\exp[B_{25/80}(1/T_2-1/(298.15K))]$		3468		K
B-value	B _{25/100}	$R_2=R_{25}\exp[B_{25/100}(1/T_2-1/(298.15K))]$		3523		K

Module

Description	Symbols	Conditions	Values	Unit
Isolation Test Voltage	V _{ISOL}	RMS, f =50Hz, t= 1min	4.0	KV
Material of Module Base plat			Cu	
Internal Isolation			Al ₂ O ₃	
Creepage Distance	d _{Creep}	Terminal to heatsink	14.5	mm
		Terminal to terminal	12.8	
Clearance	d _{Clear}	Terminal to heatsink	12.5	mm
		Terminal to terminal	10.1	
Comparative Tracking Index	CTI		200	

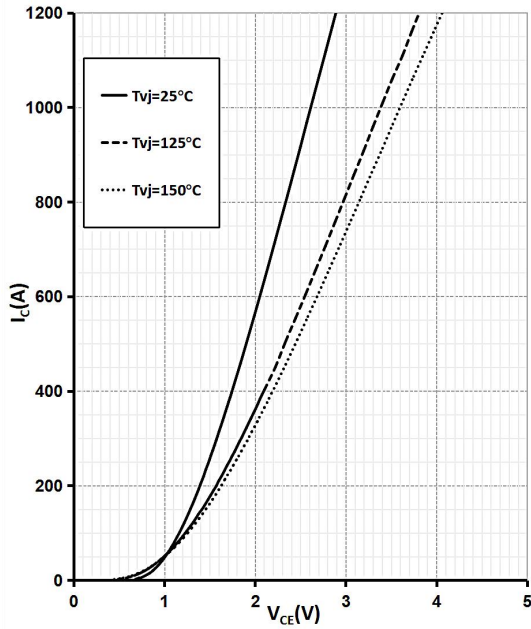
Description	Symbols	Conditions	Values			Unit
			Min	Typ	Max	
Stray Inductance Module	L _{SCE}			19		nH
Module Lead Resistance , Terminals-Chip	R _{CC'+EE'}	T _C = 25°C, Per switch		1.05		mΩ
Mounting Torque for Module Mounting	M	Screw M5	3.0		6.0	Nm
Weight	G			348		g

Thermal resistance

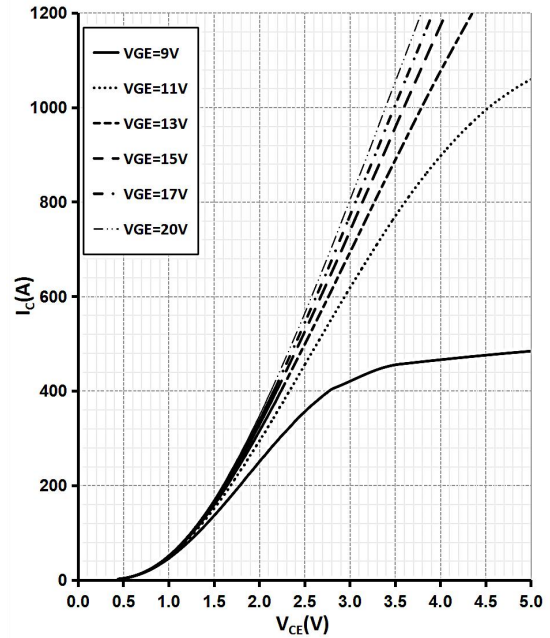
Items	Symbols	Values			Unit
		Min	Typ	Max	
Thermal Resistance, Per IGBT Junction to Case	R _{th(j-c)}			0.081	K/W
Thermal Resistance, Per Diodes Junction to Case	R _{th(j-c)}			0.136	

Output characteristic (typical), IGBT, Inverter

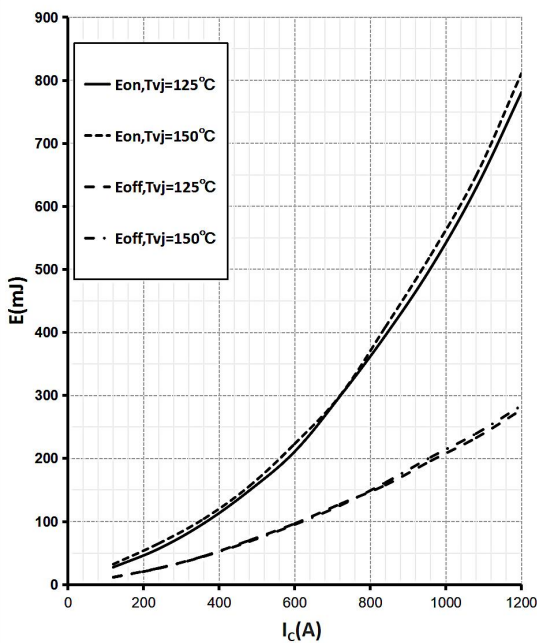
$I_C = f(V_{CE})$

 $V_{GE} = 15V$

Output characteristic (typical), IGBT, Inverter

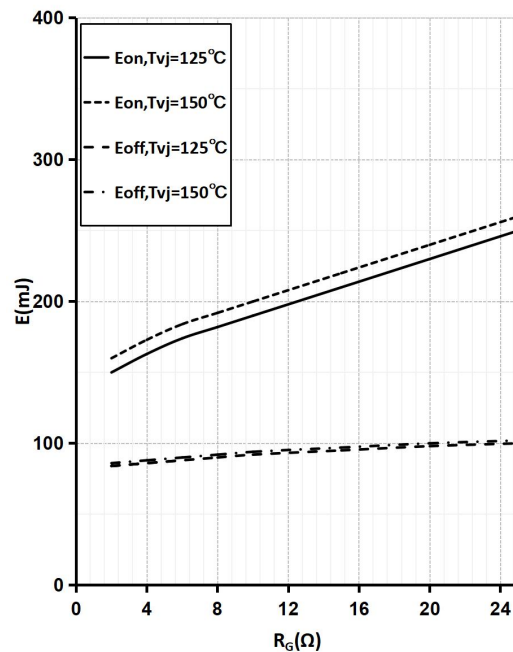
$I_C = f(V_{CE})$

 $T_{vj} = 150^{\circ}C$

Switching losses (typical), IGBT, Inverter

$E = f(I_C)$

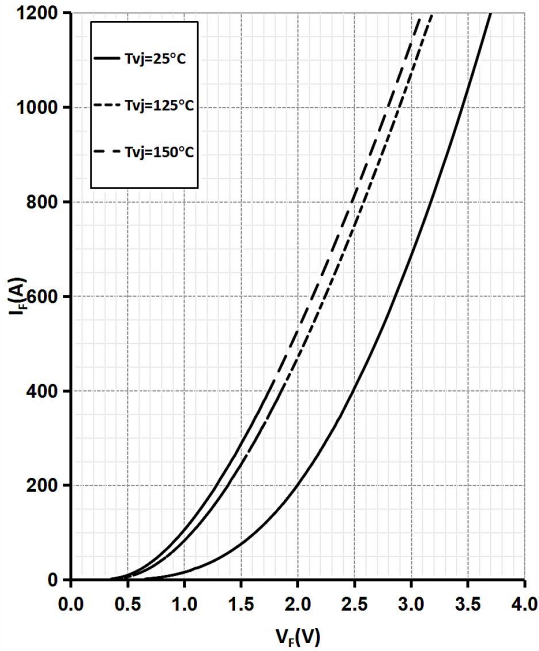
 $R_{Goff} = 15\Omega, R_{Gon} = 15\Omega, V_{GE} = \pm 15V, V_{CC} = 600V$

Switching losses (typical), IGBT, Inverter

$E = f(R_G)$

 $V_{GE} = 15V, I_C = 600A, V_{CC} = 600V$


Forward characteristic (typical), Diode, Inverter

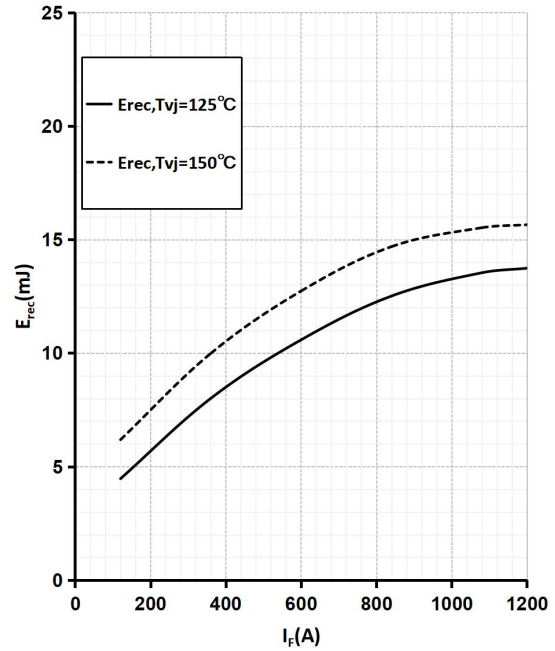
$$I_F = f(V_F)$$



Switching losses (typical), Diode, Inverter

$$E_{rec} = f(I_F)$$

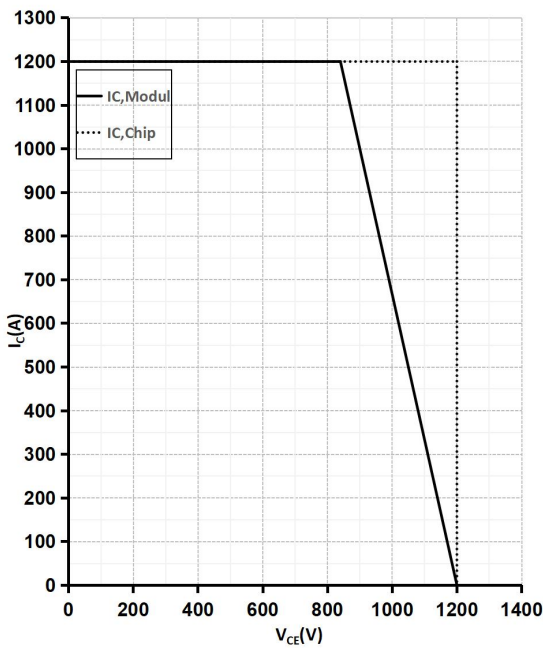
$$R_{Gon} = 15\Omega, V_{CC} = 600V$$



Reverse bias safe operating area (RBSOA), IGBT, Inverter

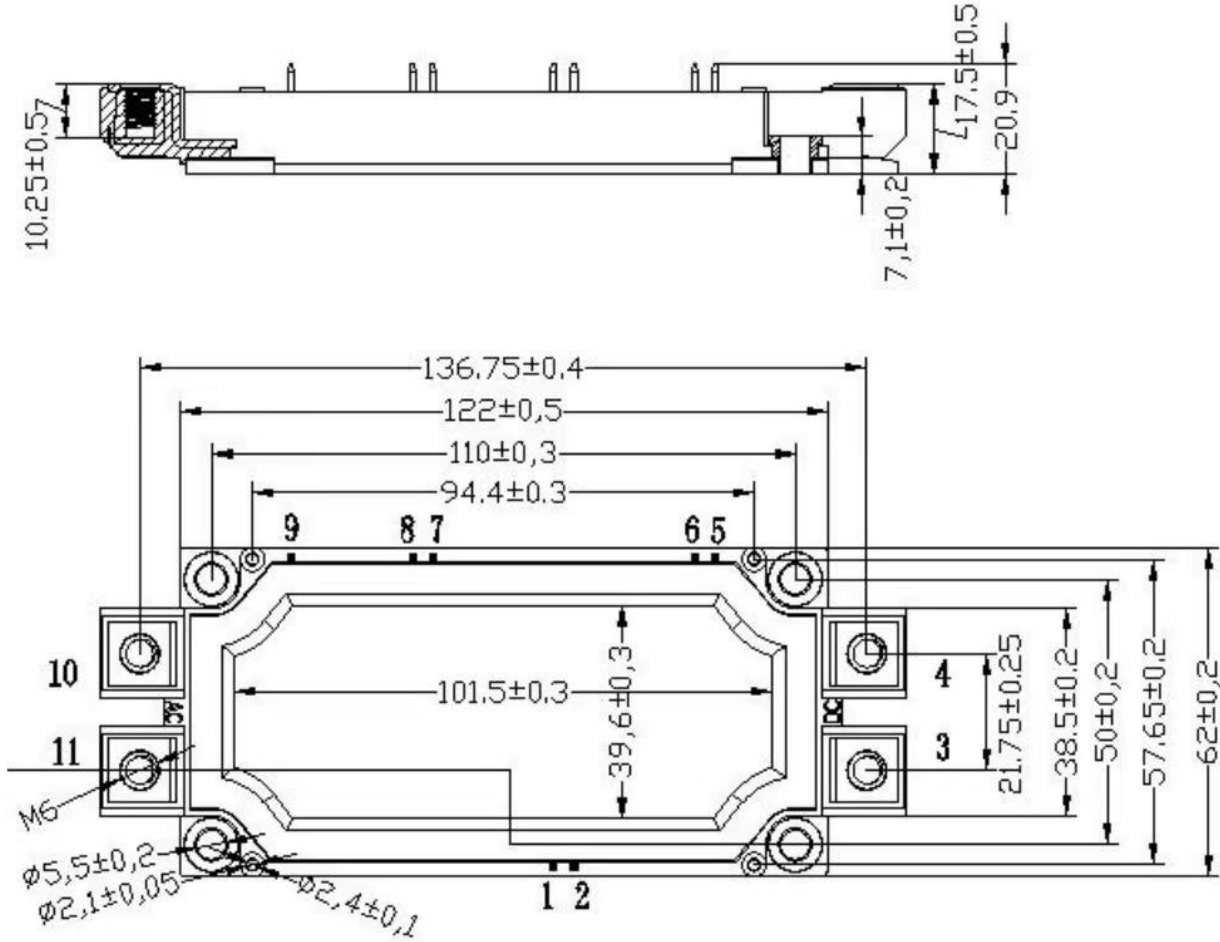
$$I_C = f(V_{CE})$$

$$R_{Goff} = 15\Omega, V_{GE} = \pm 15V, T_{vj} = 150^\circ C$$

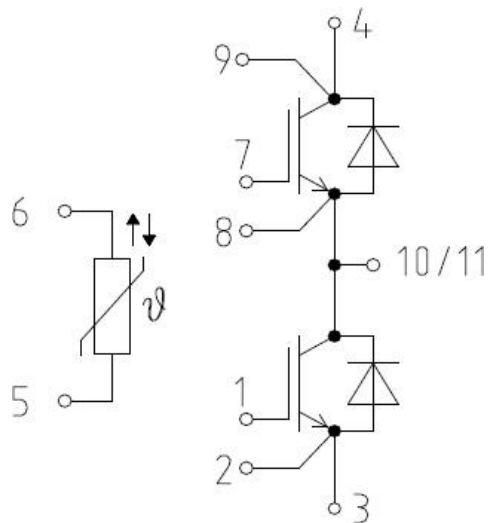


Package Dimension

Dimensions in Millimeters



Internal Circuit



Revision History

Revision	Date	Subjects (major changes since last revision)
0.1	2023-04-09	Preliminary version
1.0	2023-11-23	MP version

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